

ANx PicoOne Laser Series



KEY FEATURES

- 1064nm, 532nm, 355nm* and 266nm*
- Ultra-short pulses, down to 650ps@100kHz
- Peak power >38kW at 1064nm
- Excellent beam quality TEM00, M²<1.2
- · Efficient, air-cooled
- Sealed package, long life
- * Refer to Factory for Detailed Performance

The PicoOne amplified laser series is based on a microchip seeder and an efficient MOFA (Master Oscillator Fiber Amplifier) amplification stage, this laser produces 650 ps pulses at frequencies in excess of 100 kHz with an average power reaching 1W at 532nm. The laser operates with a single emission frequency.

The Passively Q-Switched (PQS) microchip laser technology and fiber amplification brought together with this laser series offers a full control over the pulse energy (or peak power) while leaving unchanged the pulse width and pulse shape. Other seeders may also be used if different characteristics are required.

APPLICATIONS

- Micromachining
 - Selective ablation of μm to nm scale layers
 - PCB Repair

- Instrumentation
 - Raman spectroscopy
 - Supercontinuum generation
 - Ranging
 - LIDAR

- Biophotonics
 - Dense tissue ablation



TECHNICAL SPECIFICATIONS

	ANP-20E-000	ANG-10E-000	
Wavelength	1064 nm	532 nm	
Repetition Rate	>70 kHz ⁽⁶⁾	>70 kHz ⁽⁶⁾	
Constant Pulse width range (FWHM) (1)	<0.65 ns	<0.65 ns	
Output power ⁽²⁾	>1750 mW	>700 mW	
Output energy	>25µJ ⁽⁷⁾	>10µJ ⁽⁸⁾	
Peak Power	>38kW	>15kW	
Short term(10min) power stability ⁽³⁾	<±2% rms	<±2% rms	
Long term (6 hrs) power stability ⁽³⁾	<±3% rms	<±3% rms	
Beam profile	Gaussian TEM00	Gaussian TEM00	
Full angle divergence @1/e² Horizontal Vertical M² ⁽⁴⁾	TBD TBD <1.2	TBD TBD <1.2	
Beam ellipticity ⁽⁵⁾	<1.30	<1.5	
Polarization	Linear PER>20dB	Linear PER>20dB	
Energy control function	RS232, Analog 0-5V	RS232, Analog 0-5V	
Gating function	TTL 0-5V	TTL 0-5V	
Options (described on page 3)	-x S x, -xx I	-x S x, -xx Y	

NOTES

- (1) Measured with 25Ghz photodiode and 6GHz oscilloscope.
- (2) Measurement performed with an OPHIR thermal power sensor (OPHIR 3A-FS-SH)
- (3) For temperature variation < ± 3°C and < 3°C/hour, stability is measured with calorimeter detector band [DC, 2Hz]
- (4) Mean average value $M = \sqrt{(XY)}$, X and Y being respectively the major and minor axis of the ellipse
- (5) Beam ellipticity is calculated as the ratio of the main axis far field divergence
- (6) The repetition rate can be factory-set to any fixed higher (up to 100 kHz) or lower (down to 30 kHz) value. The energy per pulse would decrease / increase accordingly.
- (7) The energy per pulse of the ANP-20E-000 can be factory-set up to 30µJ, the repetition rate would have to be decreased
- (8) The energy per pulse of the ANG-10E-000 can be factory-set up to $15\mu J$, the repetition rate would have to be decreased



SUPPLEMENTAL INFORMATION & OPTIONS

Environment Parameters		
Operating Temperature Range	15-30°C	
Maximum Power Consumption	<25W	
Storage Temperature	0-50°C	
Shock of 11ms according to IEC 68-2-27, non operating	25g	
Vibration 5Hz to 500Hz sinusoïdal according to IEC 68-2-6	2g	

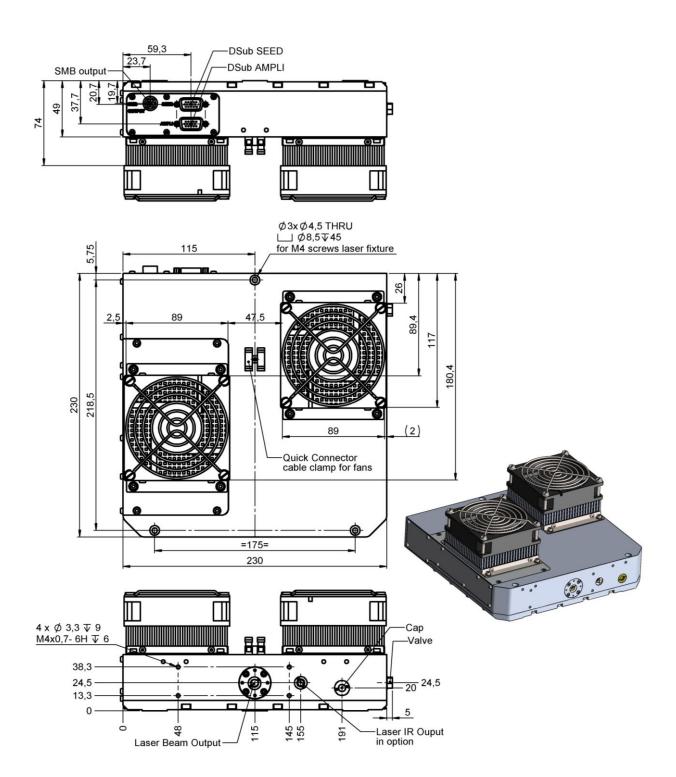
Certification		
Laser classification according to IEC 60825-1:2007	4	
CDRH compliance	In Process	
RoHs	Yes	

Package		
Laser Head dimensions, LxWxH ⁽⁷⁾	See mechanical drawings on page 4	
Laser Head weight	4.5 kgs	
Controller dimensions, LxWxH	See mechanical drawings on page 5	
Controller weight	1.1 kgs	

Options		
Synchronization output (-xSx)	TTL compatible output signal for synchronization/monitoring	
Optical Isolator option (-xxl)	1064 nm return signal Optical Isolator added inside the laser head	
Additional Infrared Output for Synchronization (-xxY)	Additional output emitting Infrared 1064nm light that can be used for Synchronization/Monitoring. The performances of this 1064nm light are not factory tested, and consequently not specified.	



LASER HEAD MECHANICAL DRAWINGS





CONTROLLER MECHANICAL DRAWINGS

